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U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

12/11	C. Hayzelden et al., "In Situ Transmission Electron Microscopy Studies of Silicide-Mediated Crystallization of Amorphous Silicon" (3 pages) <i>no date or publication source</i>
1.	A.V. Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals", (Akademikian Lavrentev Prospekt 13, 630090 Novosibirsk 90, USSR) pp. 635-640. <i>Phys. Stat. Sol. (a) 95, (1986)</i> ^(no month)
	T. Hempel et al., "Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films", <i>Solid State Communications</i> , Vol. 85, No. 11, pp. 921-924, 1993. <i>March</i>
	R. Kakkad et al., "Crystallized Si films by low-temperature rapid thermal annealing of amorphous silicon," <i>J. Appl. Phys.</i> , 65(5), March 1, 1989, pp. 2069-72.
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12/11	R. Kakkad et al., "Low Temperature Selective Crystallization of Amorphous Silicon," <i>Journal of Non-Crystalline Solids</i> , 115, 1989, pp. 66-68. <i>(no month)</i>

Examiner M. R. East

Date Considered 1/6/96

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